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Γ.	L16	L15 and (HSG or hemispherical)				
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Γ	L12	(L11 or L9 or L8 or L7)	1175			
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Π.:	L8	438/398.ccls.	801			
П	L7	(L5 or L6) and (HSG or (hemispherical adj grain\$2))	898			
<u> </u>	L6	257/532,534.ecls.	2129			
Γ:	L5	438/396-399.ccls.	5318			
Γ.	L4	((HSG with (etch\$5 or HF)) same (native adj oxide)) and (aluminum adj oxide) and nitride	6			
	L3	L2 and HF	44			
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IEEE STD	ILLE Standard		Volume 47, Issue 3, March 2000 Page(s):584 - 592				
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